



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#5/A
BEP
127-03

Applicant(s): Yoo, Woo Sik
Assignee: WaferMasters, Inc.
Title: Gas-Assisted Rapid Thermal Processing
Serial No.: 10/005,827 Filing Date: November 8, 2001
Examiner: Cothorn, Judith Group Art Unit: 2822
Docket No.: M-11914 US

BOX AMENDMENT
COMMISSIONER FOR PATENTS
Washington, D. C. 20231

Irving, California
January 13, 2003

TECHNOLOGY CENTER 2800

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RESPONSE TO OFFICE ACTION

Dear Sir:

In response to the Office Action dated October 24, 2002, Applicants submit the following amendments and remarks.

IN THE CLAIMS

The following is a clean version of the entire set of pending claims. In accordance with 37 C.F.R. § 1.121(c)(1)(ii), Attachment A provides marked up versions of the claims containing the newly introduced changes.

1. (Amended) A system for processing a semiconductor device, the system comprising:
a processing chamber defining a processing area; and
a first plate positioned within said processing chamber and defining a first internal cavity configured to receive a first gas through a first passage into said first internal cavity at a first temperature and to emit said first gas from said first internal cavity into said processing area at a second temperature through a second passage.

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